

# TRANSISTOR MODULE

## SQD400AA100

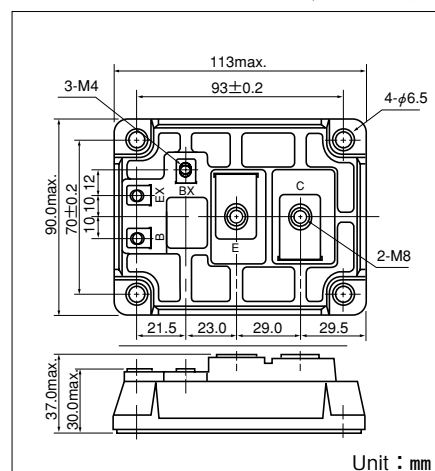
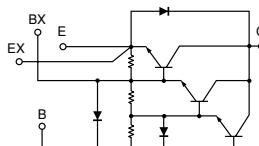
UL:E76102(M)

**SQD400AA100** is a Darlington power transistor module with a high speed, high power Darlington transistor. The transistor has a reverse paralleled fast recovery diode. The mounting base of the module is electrically isolated from Semiconductor elements for simple heatsink construction.

- $I_C=400A$ ,  $V_{CEX}=1000V$
- Low saturation voltage High DC current gain
- Isolated monuting base

### (Applications)

Motor Control (VVVF), AC/DC Servo, UPS,  
Switching Power Supply, Ultrasonic Application



Unit : mm

### Maximum Ratings

( $T_j=25^{\circ}C$  unless otherwise specified)

Symbol	Item	Conditions	Ratings	Unit
			<b>SQD400AA100</b>	
$V_{CBO}$	Collector-Base Voltage		1000	V
$V_{CEX}$	Collector-Emitter Voltage	$V_{BE}=-2V$	1200	V
$V_{CEX(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=-80A$ , $I_B=-18A$	1000	V
$V_{EBO}$	Emitterr-Base Voltage		10	V
$I_C$	Collector Current		400	A
$-I_C$	Reverse Collector Current		400	A
$I_B$	Base Current		20	A
$P_T$	Total power dissipation	$T_C=25^{\circ}C$	3120	W
$T_j$	Junction Temperature		-40 to +150	$^{\circ}C$
$T_{stg}$	Storage Temperature		-40 to +125	$^{\circ}C$
$V_{iso}$	Isolation Voltage	A.C. 1minute	2500	V
	Mounting Torque	Mouting (M6)	Recommended Value 2.5-3.9 (25-40)	N·m (kgf·cm)
		Terminal (M8)	Recommended Value 8.8-10 (90-105)	
		Terminal (M4)	Recommended Value 1.0-1.4 (10-14)	
	Mass	Typical Value	670	g

### Electrical Characteristics

Symbol	Item	Conditions	Ratings		Unit
			Min.	Max.	
$I_{CBO}$	Collector Cut-off Current	$V_{CB}=1000V$		3.0	mA
$I_{EBO}$	Emitter Cut-off Current	$V_{EB}=10V$		1000	mA
$h_{FE}$	DC Current Gain	$I_C=300A$ , $V_{CE}=2.8V$	75		
		$I_C=400A$ , $V_{CE}=5V$	100		
$V_{CE(sat)}$	Collector-Emitter Sturation Voltage	$I_C=400A$ , $I_B=8A$		2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=400A$ , $I_B=8A$		3.5	V
$t_{on}$	Switching Time	On Time		3.0	$\mu s$
$t_s$		Storage Time		16.0	
$t_f$		Fall Time		3.0	
$V_{ECO}$	$I_C=-400A$	Collector-Emitter Reverse Voltage		1.8	V
$R_{th(j-c)}$	Thermal Impedance (junction to case)	Transistor part		0.04	$^{\circ}C/W$
		Diode part		0.16	

